

Prospective Data

Insulated Gate Bi-Polar Transistor

Type T0900DF65A

Absolute Maximum Ratings

	VOLTAGE RATINGS	MAXIMUM LIMITS	UNITS
V_{CES}	Collector – emitter voltage	6500	V
V_{CES}	Collector – emitter voltage (T_j 25°C)	6500	V
V_{CES}	Collector – emitter voltage (T_j -40°C)	6000	V
$V_{DC\ link}$	Permanent DC voltage for 100 FIT failure rate	3600	V
V_{GES}	Peak gate – emitter voltage	±20	V

	RATINGS	MAXIMUM LIMITS	UNITS
I_C	DC collector current, IGBT	900	A
I_{CRM}	Repetitive peak collector current, $t_p=1ms$, IGBT	1800	A
$I_{F(DC)}$	Continuous DC forward current, Diode	900	A
I_{FRM}	Repetitive peak forward current, $t_p=1ms$, Diode	1800	A
I_{FSM}	Peak non-repetitive surge $t_p=10ms$, $V_{RM}=60\%V_{RRM}$, Diode (Note 4)	7680	A
I_{FSM2}	Peak non-repetitive surge $t_p=10ms$, $V_{RM}\leq 10V$, Diode (Note 4)	8450	A
P_{MAX}	Maximum power dissipation, IGBT (Note 2)	10.6	kW
$(di/dt)_{cr}$	Critical diode di/dt (note 3)	2500	A/μs
T_j	Operating temperature range.	-40 to +125	°C
T_{stg}	Storage temperature range.	-40 to +125	°C

Notes: -

- 1) Unless otherwise indicated $T_j = 125^\circ C$.
- 2) $T_{sink} = 25^\circ C$, double side cooled.
- 3) Maximum commutation loop inductance 200nH.
- 4) Half-sinewave, 125°C T_j initial.

Characteristics

IGBT Characteristics

	PARAMETER	MIN	TYP	MAX	TEST CONDITIONS	UNITS
$V_{CE(sat)}$	Collector – emitter saturation voltage	-	3.6	-	$I_C = 900A, V_{GE} = 15V, T_j = 25^\circ C$	V
		4.4	4.8	5.2	$I_C = 900A, V_{GE} = 15V$	V
V_{T0}	Threshold voltage	-	-	2.49	Current range: 300A – 900A	V
r_T	Slope resistance	-	-	3.02		m Ω
$V_{GE(TH)}$	Gate threshold voltage	-	5.2	-	$V_{CE} = V_{GE}, I_C = 900mA$	V
I_{CES}	Collector – emitter cut-off current	-	10	35	$V_{CE} = V_{CES}, V_{GE} = 0V$	mA
I_{GES}	Gate leakage current	-50	-	+50	$V_{GE} = \pm 20V$	μA
C_{ies}	Input capacitance	-	160	-	$V_{CE} = 10V, V_{GE} = 0V, f = 100kHz, T_j = 25^\circ C$	nF
$t_{d(on)}$	Turn-on delay time	-	2.1	-	$I_C = 900A, V_{CE} = 3600V, di/dt = 1500A/\mu s$ $V_{GE} = \pm 15V, L_s = 280nH$ $R_{g(ON)} = 4.7\Omega, R_{g(OFF)} = 14\Omega, C_{GE} = 133nF$ Integral diode used as freewheel diode (Note 3 & 4)	μs
$t_r(V)$	Rise time	-	2.5	-		μs
$Q_{g(on)}$	Turn-on gate charge	-	6	-		μC
E_{on}	Turn-on energy	-	9.5	-		J
$t_{d(off)}$	Turn-off delay time	-	4.5	-		μs
$t_f(I)$	Fall time	-	2.3	-		μs
$Q_{g(off)}$	Turn-off gate charge	-	5	-		μC
E_{off}	Turn-off energy	-	5.7	-		J
I_{SC}	Short circuit current	-	4900	-	$V_{GE} = +15V, V_{CC} = 3600V, V_{CEmax} \leq V_{CES}, t_p \leq 10\mu s$	A

Diode Characteristics

	PARAMETER	MIN	TYP	MAX	TEST CONDITIONS	UNITS
V_F	Forward voltage	-	3	-	$I_F = 900A, T_j = 25^\circ C$	V
		-	3.4	3.8	$I_F = 900A$	V
V_{T0}	Threshold voltage	-	-	1.89	Current range 300A – 900A	V
r_T	Slope resistance	-	-	2.12		m Ω
I_{rm}	Peak reverse recovery current	-	660	-	$I_F = 900A, V_{GE} = -15V, di/dt = 1500A/\mu s$	A
Q_{rr}	Recovered charge	-	1550	-		μC
t_{rr}	Reverse recovery time, 50% chord	-	1.7	-		μs
E_r	Reverse recovery energy	-	3.4	-		J

Thermal Characteristics

	PARAMETER	MIN	TYP	MAX	TEST CONDITIONS	UNITS
R_{thJK}	Thermal resistance junction to sink, IGBT	-	-	9.4	Double side cooled	K/kW
		-	-	14.3	Collector side cooled	K/kW
		-	-	27.6	Emitter side cooled	K/kW
R_{thJK}	Thermal resistance junction to sink, Diode	-	-	16	Double side cooled	K/kW
		-	-	23.4	Cathode side cooled	K/kW
		-	-	50.6	Anode side cooled	K/kW
F	Mounting force	45	-	55	Note 2	kN
W_t	Weight	-	1.5	-		kg

Notes:-

- 1) Unless otherwise indicated $T_j = 125^\circ C$.
- 2) Consult application note 2008AN01 for detailed mounting requirements
- 3) C_{GE} is additional gate – emitter capacitance added to output of gate drive
- 4) Data are obtained using integral diode as freewheeling diode

Curves

Figure 1 – Typical collector-emitter saturation voltage characteristics

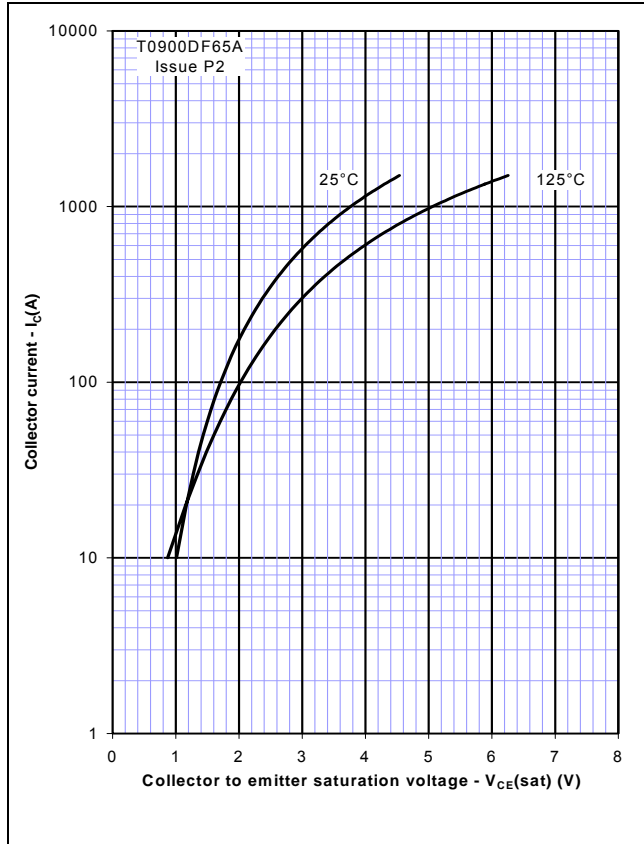


Figure 2 – Typical output characteristics

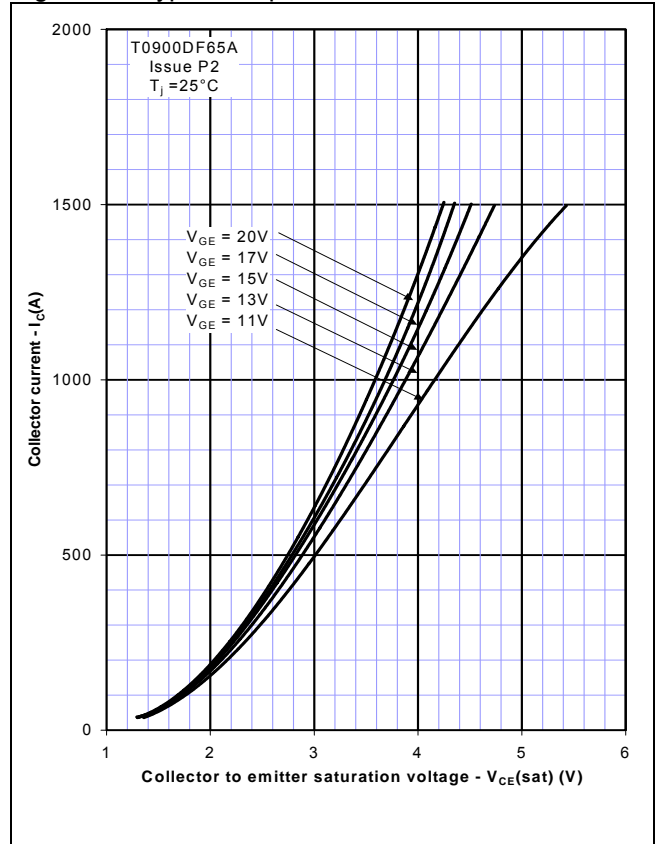


Figure 3 – Typical output characteristics

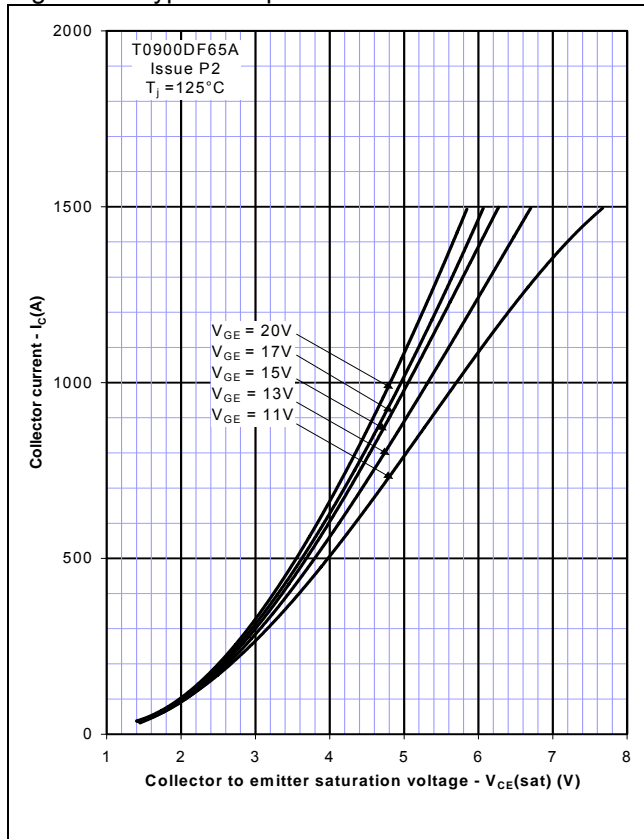


Figure 4 – Typical diode forward characteristics

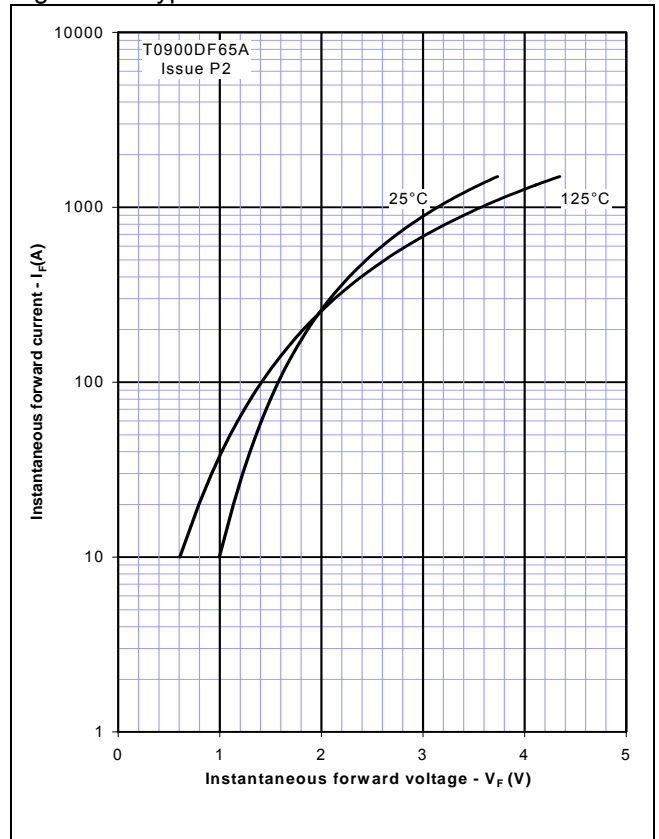


Figure 5 – Safe operating area (IGBT)

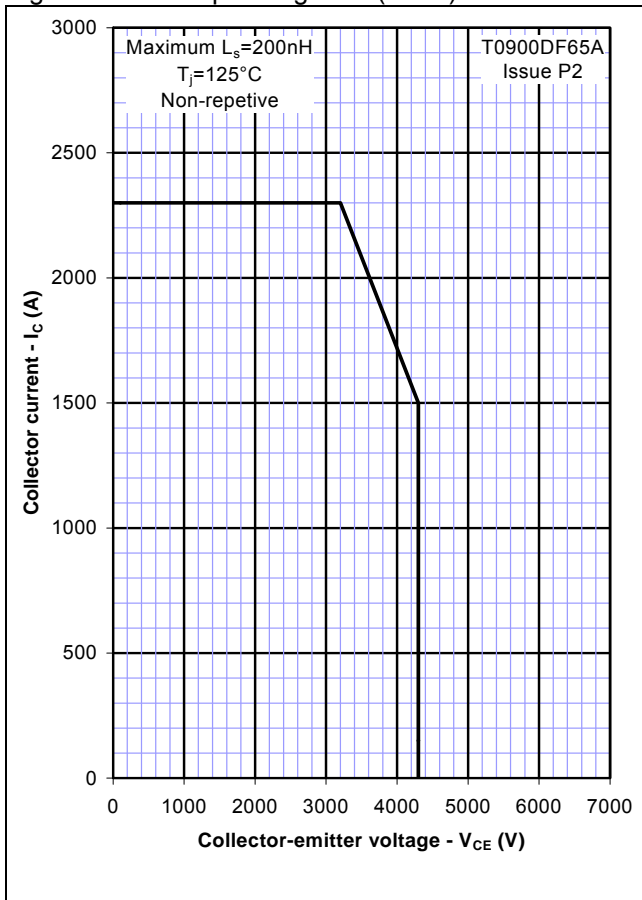


Figure 6 – Safe operating area (Diode)

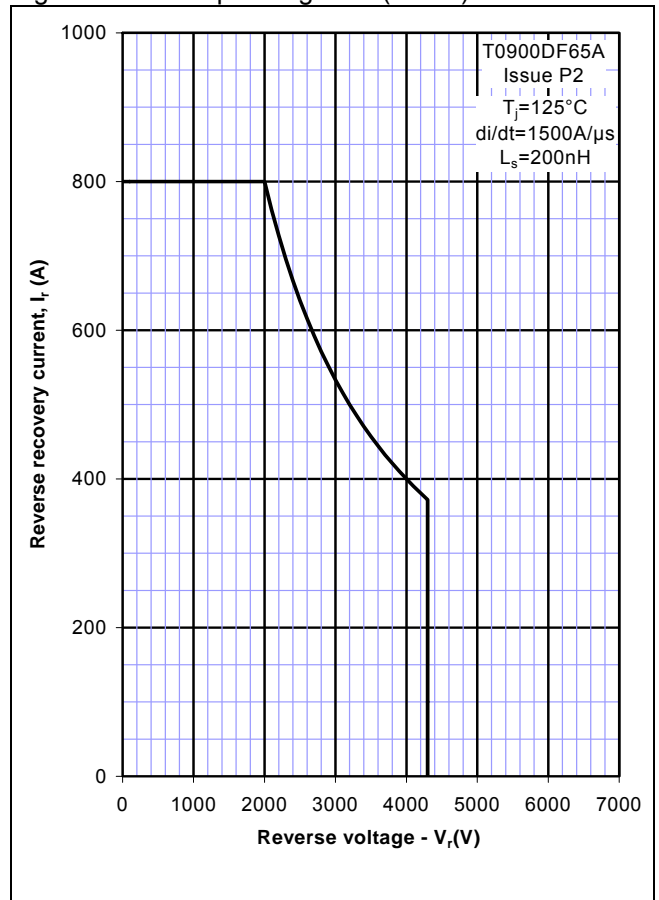


Figure 7 – Transient thermal impedance (IGBT)

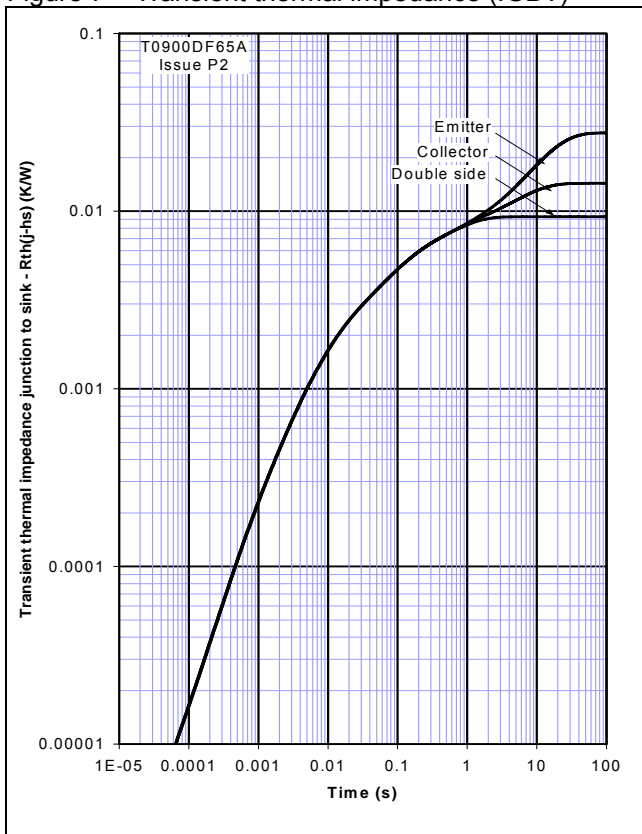
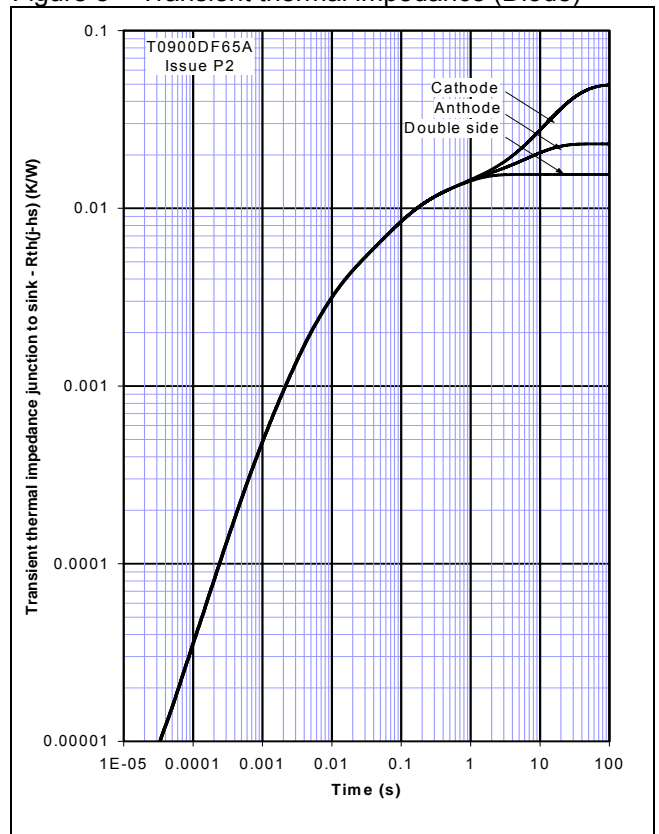
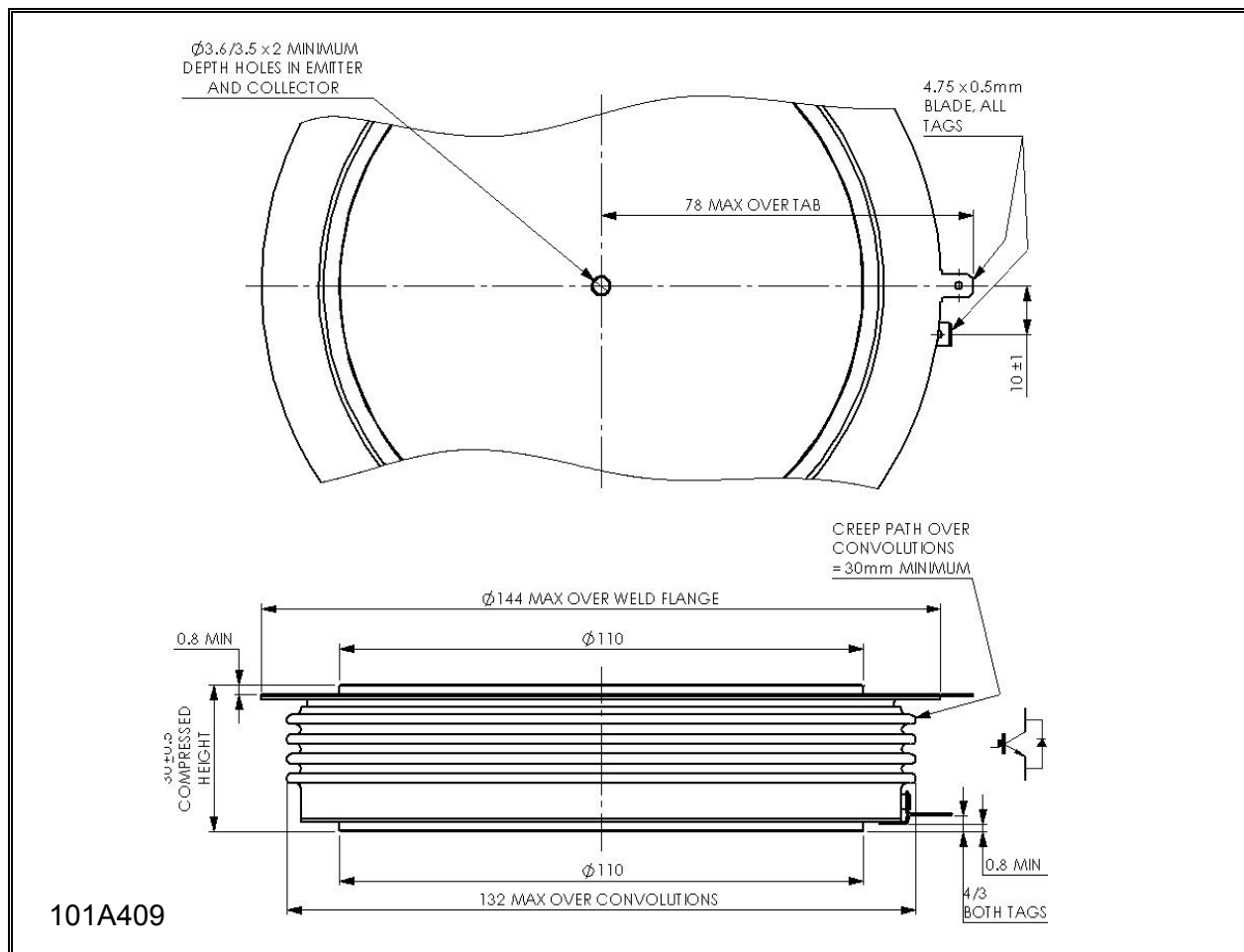


Figure 8 – Transient thermal impedance (Diode)



Outline Drawing & Ordering Information



ORDERING INFORMATION

(Please quote 10 digit code as below)

T0900	DF	65	A
Fixed type Code	Fixed Outline Code	Voltage Grade $V_{CES}/100$ 65	Fixed format code

Typical order code: T0900DF65A ($V_{CES} = 6500V$)

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